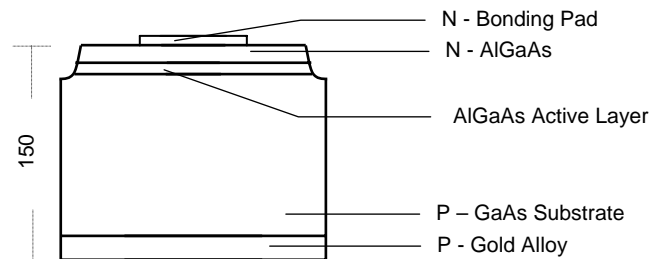
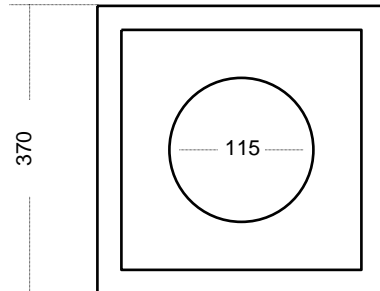


TCD810

❖ Outline Dimensions:

Unit: μm



❖ Physical Structure:

Chip dimensions	Chip size	15 mil x 15 mil	370 μm x 370 μm
	Thickness	6 mil	150 μm
	Bonding pad	4.5 mil	115 μm

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	-	1.80	V
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Peak Wavelength	λ_P	$I_F = 20\text{mA}$	-	810	-	nm
Radiant Flux	P_O	$I_F = 20\text{mA}$	1.0	-	-	mW